



TPDV640 ---> TPDV1240

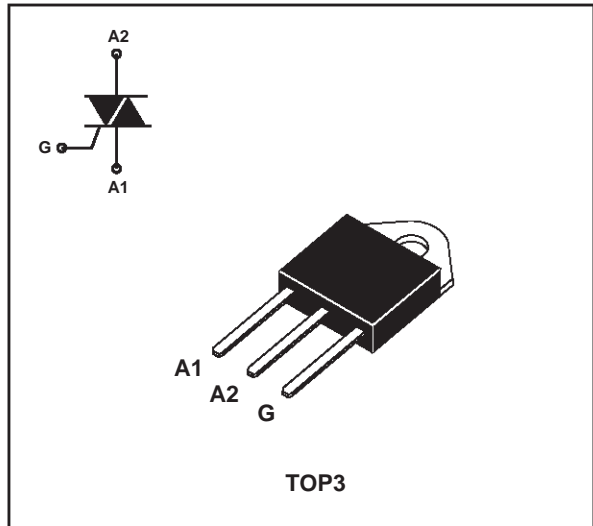
ALTERNISTORS

FEATURES

- High commutation: > 142A/ms (400Hz)
- Insulating voltage = 2500V_(RMS)
(UL Recognized: EB81734)
- High voltage capability: V_{DRM} = 1200V

DESCRIPTION

The TPDV640 ---> TPDV1240 use a high performance passivated glass alternistor technology. Featuring very high commutation levels and high surge current capability, this family is well adapted to power control on inductive load (motor, transformer...)



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
I _{T(RMS)}	RMS on-state current (360° conduction angle)	T _c = 75°C 40	A
I _{TSM}	Non repetitive surge peak on-state current (T _j initial = 25°C)	tp = 2.5ms 590 tp = 8.3ms 370 tp = 10ms 350	A
I ² t	I ² t value	tp = 10ms 610	A ² s
di/dt	Critical rate of rise of on-state current Gate supply: I _G = 500mA di _G /dt = 1A/μs	Repetitive F = 50Hz 20 Non repetitive 100	A/μs
T _{stg} T _j	Storage and operating junction temperature range	-40 to +150 -40 to +125	°C
T _l	Maximum lead soldering temperature during 10s at 4.5mm from case	260	°C

Symbol	Parameter	TPDV				Unit
		640	840	1040	1240	
V _{DRM} V _{RDM}	Repetitive peak off-state voltage T _j = 125°C	600	800	1000	1200	V

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THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
Rth (j-a)	Contact to ambient	50	°C/W
Rth (j-c) DC	Junction to case for DC	1.2	°C/W
Rth (j-c) AC	Junction to case for 360° conduction angle (F = 50Hz)	0.9	°C/W

GATE CHARACTERISTICS (maximum values)

$P_{G(AV)} = 1W$ $P_{GM} = 40W$ ($t_p = 20\mu s$) $I_{GM} = 8A$ ($t_p = 20\mu s$) $V_{GM} = 16V$ ($t_p = 20\mu s$)

ELECTRICAL CHARACTERISTICS

Symbol	Test conditions	Quadrant		Value	Unit
I_{GT}	$V_D = 12V$ (DC) $R_L = 33\Omega$	$T_j = 25^\circ C$	I - II - III	MAX.	200 mA
V_{GT}	$V_D = 12V$ (DC) $R_L = 33\Omega$	$T_j = 25^\circ C$	I - II - III	MAX.	1.5 V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3k\Omega$	$T_j = 125^\circ C$	I - II - III	MIN.	0.2 V
tgt	$V_D = V_{DRM}$ $I_G = 500mA$ $di_G/dt = 3A/\mu s$	$T_j = 25^\circ C$	I - II - III	TYP.	2.5 μs
I_L	$I_G = 1.2I_{GT}$	$T_j = 25^\circ C$	I - III	TYP.	100 mA
			II		200
I_H^*	$I_T = 500mA$ Gate open	$T_j = 25^\circ C$		TYP.	50 mA
V_{TM}^*	$I_{TM} = 60A$ $t_p = 380\mu s$	$T_j = 25^\circ C$		MAX.	1.8 V
I_{DRM} I_{RRM}	V_{DRM} rated V_{RRM} rated	$T_j = 25^\circ C$		MAX.	0.02 mA
		$T_j = 125^\circ C$		MAX.	8
dV/dt *	Linear slope up to $V_D = 67\% V_{DRM}$ gate open	$T_j = 125^\circ C$		MIN.	500 V/ μs
(di/dt)c*	(dV/dt)c = 200V/ μs	$T_j = 125^\circ C$		MIN.	35 A/ms
	(dV/dt)c = 10V/ μs				142

* For either polarity of electrode A₂ voltage with reference to electrode A₁.

Fig. 1: Maximum RMS power dissipation versus RMS on-state current ($F = 50\text{Hz}$). (Curves are cut off by $(di/dt)_c$ limitation)

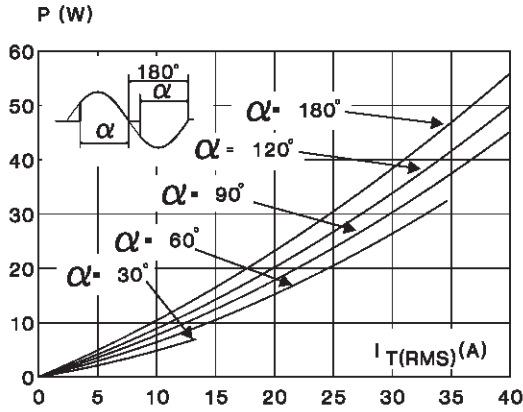


Fig. 2: Correlation between maximum RMS power dissipation and maximum allowable temperatures (T_{amb} and T_{case}) for different thermal resistances heatsink + contact.

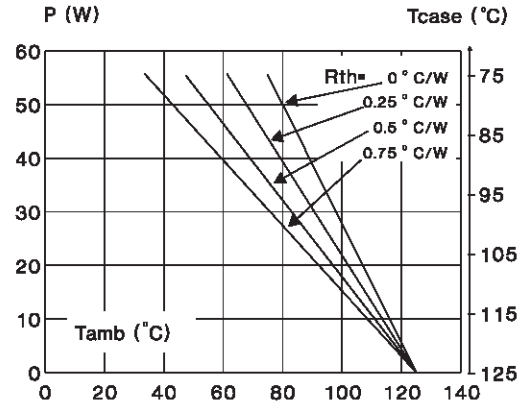


Fig. 3: RMS on-state current versus case temperature.

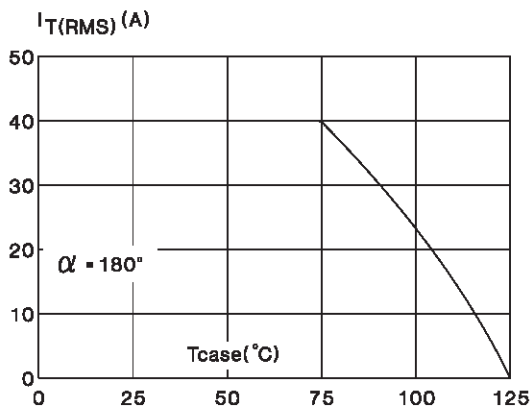


Fig. 4: Relative variation of thermal impedance versus pulse duration.

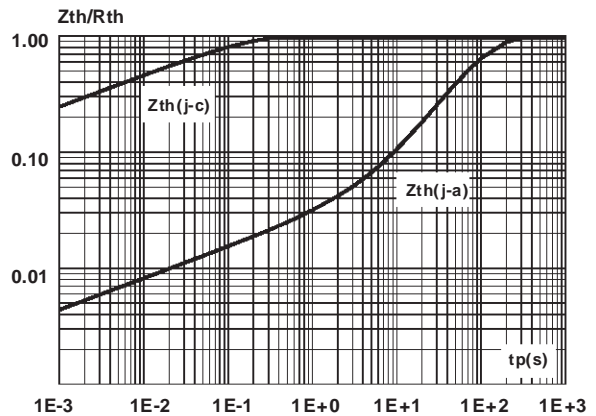


Fig. 5: Relative variation of gate trigger current and holding current versus junction temperature.

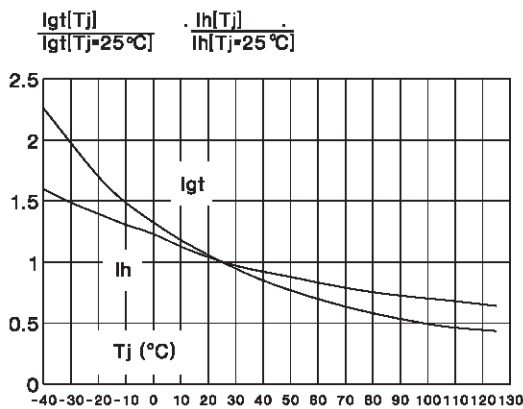


Fig. 6: Non repetitive surge peak on-state current versus number of cycles.

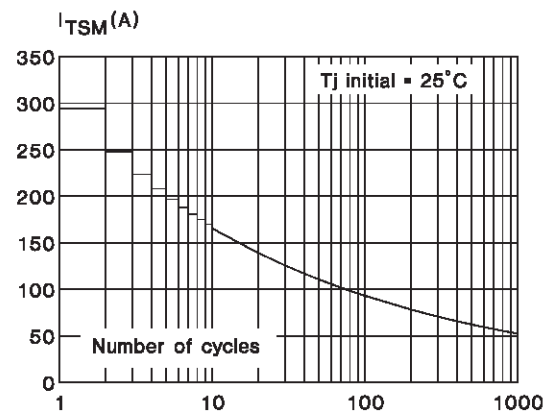


Fig. 7: Non repetitive surge peak on-state current for a sinusoidal pulse with width: $t \leq 10\text{ms}$, and corresponding value of I^2t .

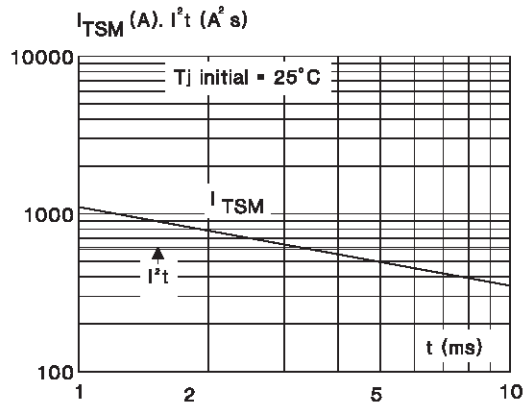


Fig. 8: On-state characteristics (maximum values).

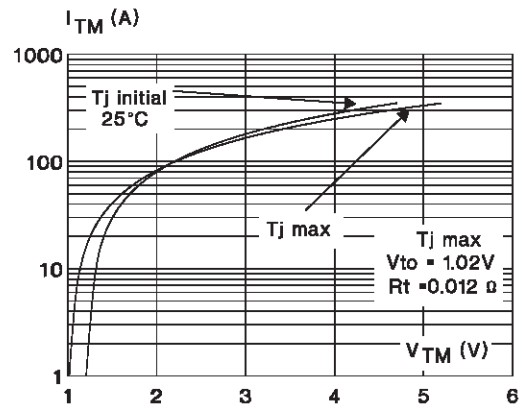
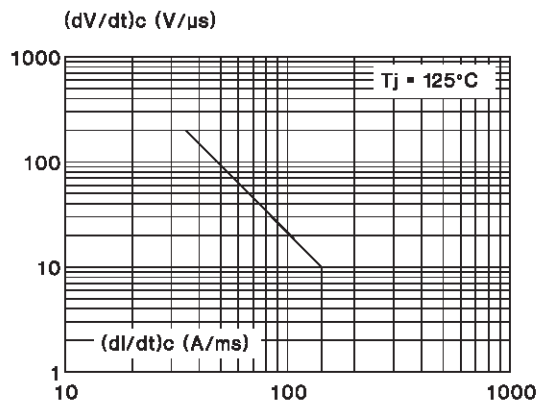
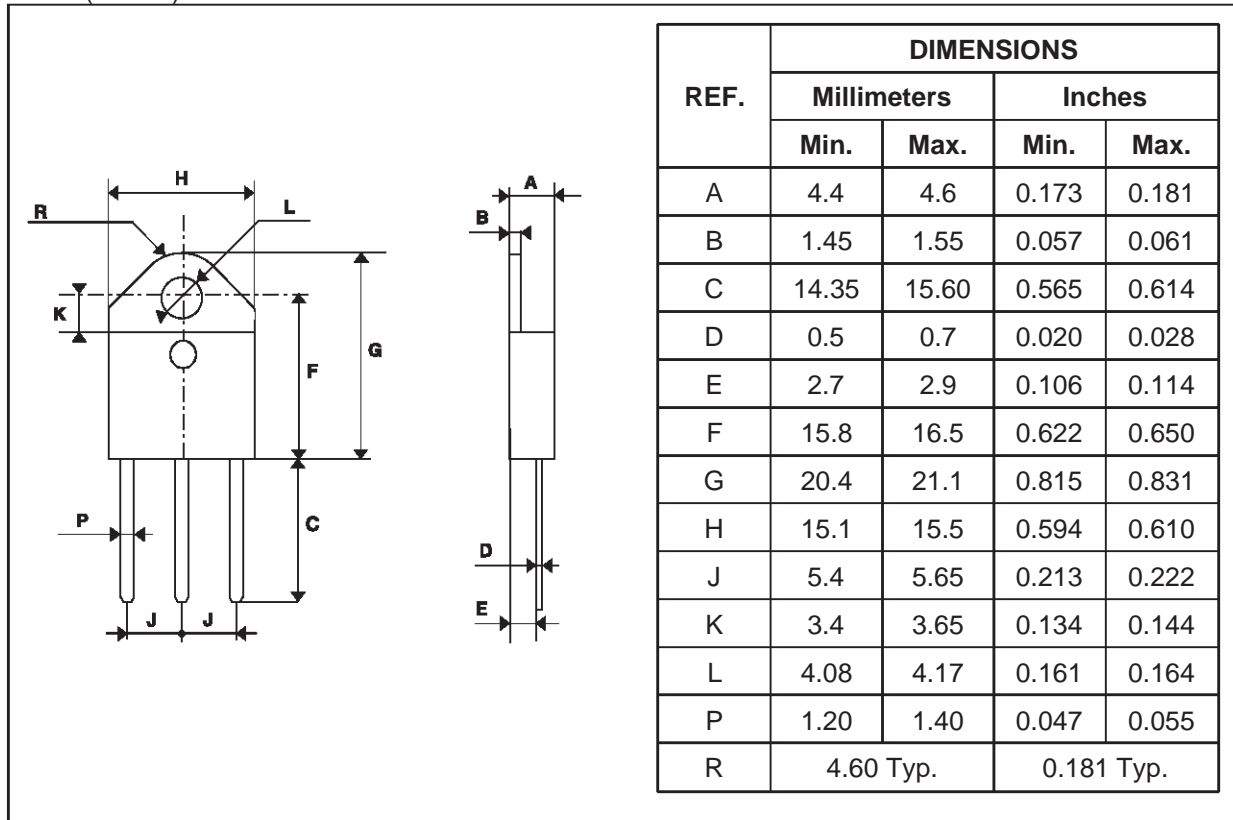


Fig. 9: Safe operating area.



PACKAGE MECHANICAL DATA
TOP3 (Plastic)



OTHER INFORMATION

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
TPDVx40	TPDVx40	TOP3	4.5 g	120	Bulk

- Epoxy meets UL94,V0
- Cooling method: C
- Recommended torque value: 0.8 m.N.
- Maximum torque value: 1 m.N.

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